NEC

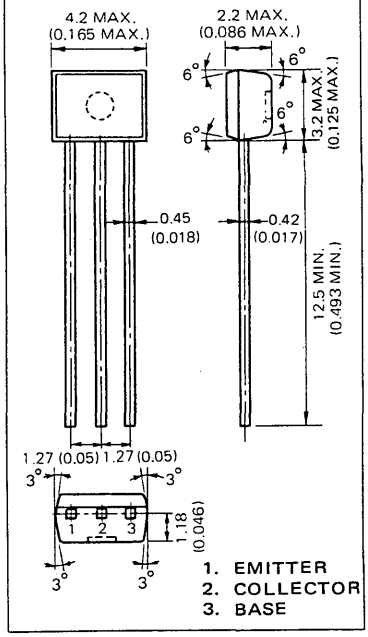
NPN SILICON TRANSISTOR
2SC2784

DESCRIPTION The 2SC2784 is the best for use as the middle range amplifier in Hi-Fi stereo control amplifiers, power amplifiers, and etc.

FEATURES

- High voltage. V_{CEO} : 120 V
- Low output capacitance. C_{ob} : 1.6 pF TYP. (V_{CB} = 30 V)
- High h_{FE} h_{FE} : 600 TYP. (V_{CE} = 6.0 V, I_C = 1.0 mA)
- Super low noise. NV : 25 mV TYP. (See test circuit.)
- Complementary to the NEC 2SA1174 PNP transistor.

PACKAGE DIMENSIONS
in millimeters (inches)



ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures
- Storage Temperature ..... −55 to +125 °C
- Junction Temperature ..... +125 °C Maximum

Maximum Power Dissipation (Ta = 25 °C)
- Total Power Dissipation ..... 300 mW

Maximum Voltages and Currents (Ta = 25 °C)
- V_{CBO} Collector to Base Voltage ..... 120 V
- V_{CEO} Collector to Emitter Voltage ..... 120 V
- V_{EBO} Emitter to Base Voltage ..... 5.0 V
- I_C Collector Current ..... 50 mA
- I_B Base Current ..... 10 mA

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE1}	DC Current Gain	150	580		–	V_{CE}=6.0 V, I_C=0.1 mA
h_{FE2}	DC Current Gain	200	600	1200	–	V_{CE}=6.0 V, I_C=1.0 mA
f_T	Gain Bandwidth Product	50	110		MHz	V_{CE}=6.0 V, I_E=1.0 mA
C_{ob}	Output Capacitance		1.6	2.5	pF	V_{CB}=30 V, I_E=0, f=1.0 MHz
NV	Noise Voltage		25	40	mV	V_{CE}=5.0 V, I_C=1.0 mA, R_G=100 kΩ, G_V=80 dB, f=10 Hz to 1.0 kHz
I_{CBO}	Collector Cutoff Current			50	nA	V_{CB}=120 V, I_E=0
I_{EBO}	Emitter Cutoff Current			50	nA	V_{EB}=5.0 V, I_C=0
V_{BE}	Base to Emitter Voltage	0.55	0.59	0.65	V	V_{CE}=6.0 V, I_C=1.0 mA
$V_{CE(sat)}$	Collector Saturation Voltage		0.07	0.30	V	I_C=10 mA, I_B=1.0 mA

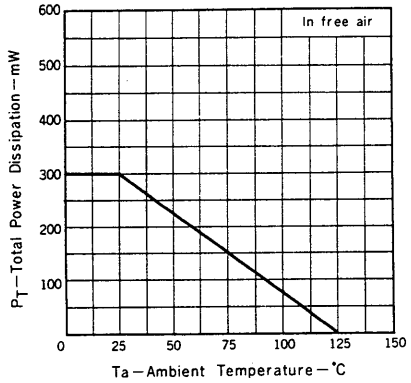
Classification of h_{FE2}

Rank	P	F	E	U
Range	200 – 400	300 – 600	400 – 800	600 – 1200

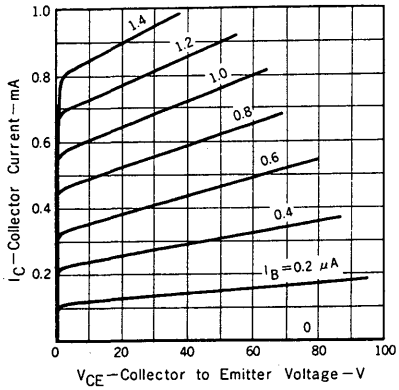
h_{FE2} Test Conditions : V_{CE} = 6.0 V, I_C = 1.0 mA

TYPICAL CHARACTERISTICS (Ta = 25 °C unless otherwise noted)

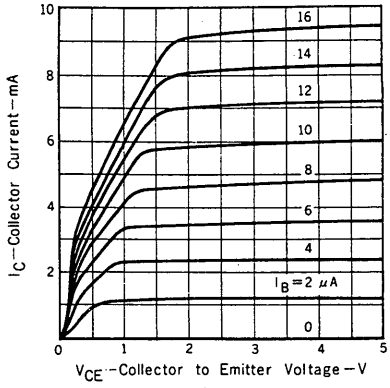
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



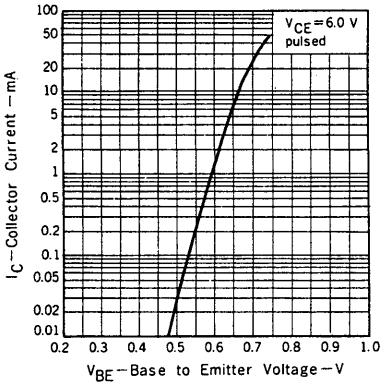
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



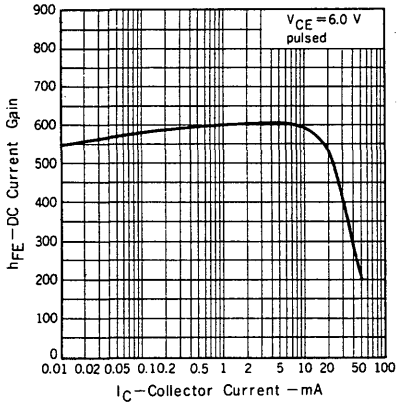
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



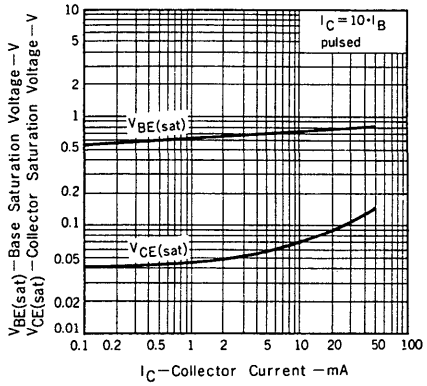
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



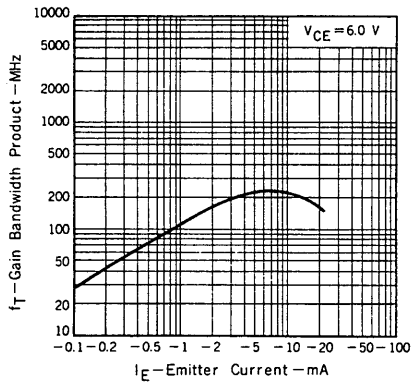
DC CURRENT GAIN vs. COLLECTOR CURRENT



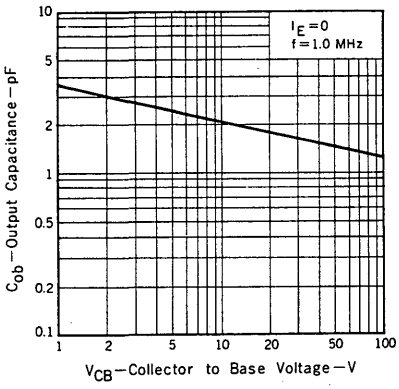
COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



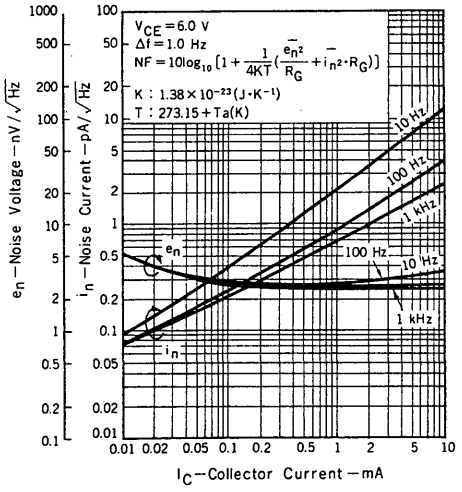
GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



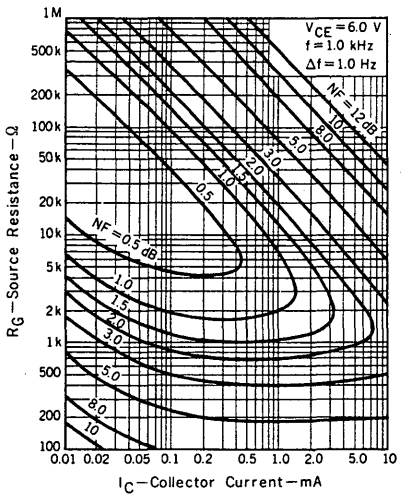
OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



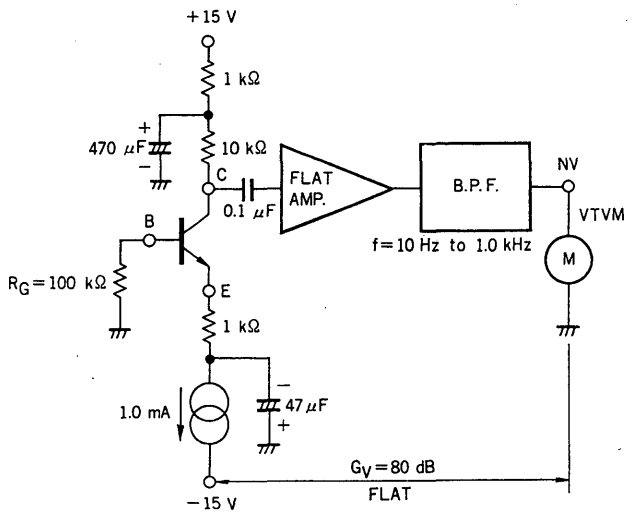
e_n AND i_n vs. COLLECTOR CURRENT



NOISE FIGURE MAP



NOISE VOLTAGE TEST CIRCUIT



$V_{CE} \fallingdotseq 5$ V, $I_C = 1.0$ mA, $R_G = 100$ kΩ, $G_V = 80$ dB, FLAT(f = 10 Hz to 1.0 kHz)